CMD280
DC-30 GHz 5-bit Digital Attenuator

Product Overview

The CMD280 is negative controlled, wideband GaAs MMIC 5-bit digital attenuator die which operates from DC to 30 GHz. Each bit of the attenuator is controlled by a single voltage of either 0 V or –5 V. The attenuator bit values are 0.5 (LSB), 1, 2, 4, and 8 dB, for a total attenuation of 15.5 dB. The CMD280 has a low insertion loss of 3 dB at 10 GHz and the attenuation accuracy is typically 0.1 dB step error. The CMD280 is a 50 ohm matched design which eliminates the need for RF port matching. The CMD280 offers full passivation for increased reliability and moisture protection.

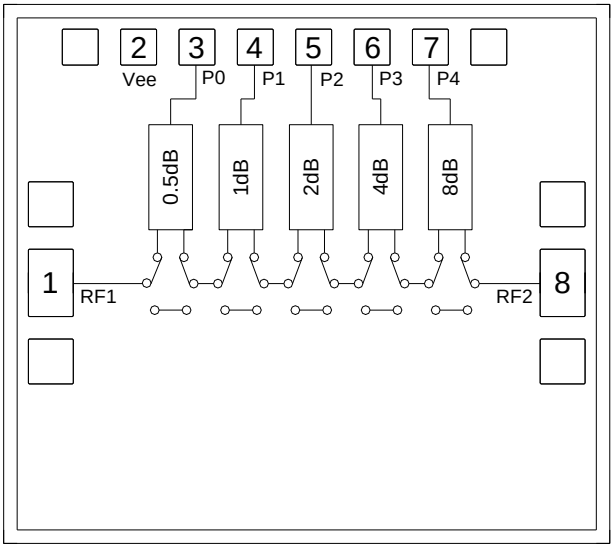
Key Features

- Ultra-Wideband Performance
- Low Insertion Loss
- Wide Attenuation Range
- Small Die Size

Ordering Information

Part No.	Description
CMD280	100 Piece Gel Pack

Functional Block Diagram



Electrical Performance (V_{ee} = -5 V, V_{ctl} = 0 / -5 V, T_A = 25° C, F = 10 GHz)

Parameter	Min	Typ.	Max	Units
Frequency Range		DC - 30		GHz
Insertion Loss		3		dB
Attenuation Range		15.5		dB
Input Return Loss		15		dB
Output Return Loss		15		dB
Input P0.1dB		24		dBm
Input IP3		42		dBm
Switching Speed		25		ns

Absolute Maximum Ratings

Parameter	Rating
Bias Voltage, V_{ee}	-8 V
Control Voltage, V_{ctl}	-8 V
RF Input Power	+27 dBm
Thermal Resistance, θ_{JC}	125.32° C/W
Operating Temperature	-55 to 85° C
Storage Temperature	-55 to 150° C

Exceeding any one or combination of the maximum ratings may cause permanent damage to the device.

Recommended Operating Conditions

Parameter	Min	Typ.	Max	Units
V_{ee}	-5.5	-5	-2.5	V

Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

Truth Table

Control Voltage Input					Attenuation State RF1 - RF2 (dB)
P0 0.5 dB	P1 1 dB	P2 2 dB	P3 4 dB	P4 8 dB	
Low	Low	Low	Low	Low	Reference (insertion loss)
High	Low	Low	Low	Low	0.5
Low	High	Low	Low	Low	1.0
Low	Low	High	Low	Low	2.0
Low	Low	Low	High	Low	4.0
Low	Low	Low	Low	High	8.0
High	High	High	High	High	15.5

Any combination of the above states will result in an attenuation approximately equal to the sum of the bits selected.

Control Voltage

State	Bias Condition
High	V_{ee} ± 0.3 V
Low	0 ± 0.3 V

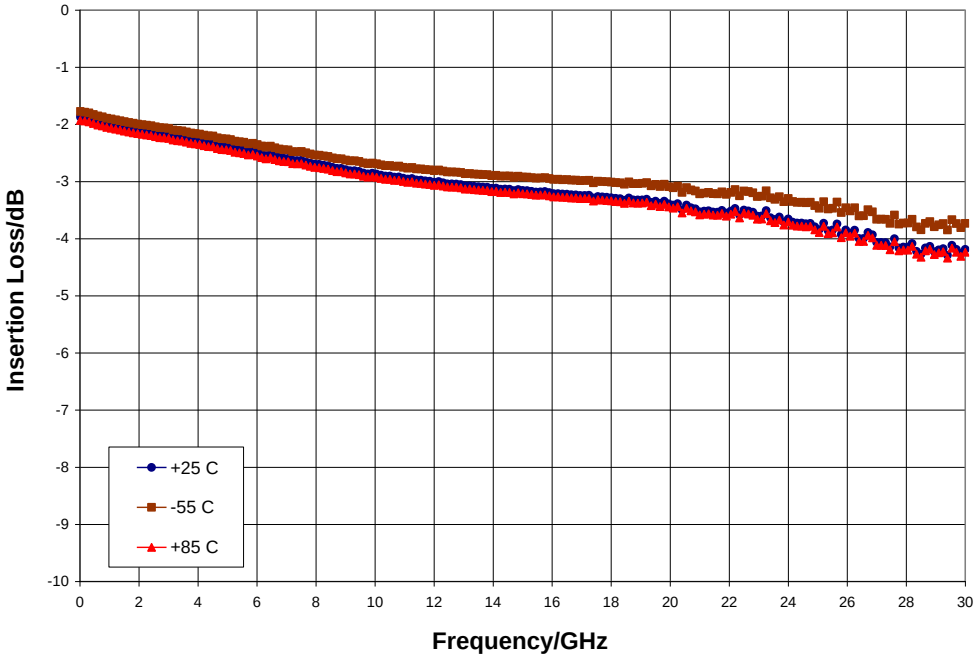
Electrical Specifications (V_{ee} = -5 V, V_{ctl} = 0 / -5 V, T_A = 25° C)

Parameter		Min	Typ.	Max	Min	Typ.	Max	Units
Frequency Range			2 - 18			18 - 30		GHz
Insertion Loss		-	2.8	4.0	-	3.7	5.0	dB
Attenuation Range		-	15.5	-	-	15.5	-	dB
Attenuation Accuracy	0.5 dB State	0.20	-	0.80	0.10	-	0.90	dB
	1 dB State	0.70	-	1.35	0.60	-	1.40	
	2 dB State	1.70	-	2.30	1.60	-	2.40	
	4 dB State	3.70	-	4.30	3.60	-	4.40	
	8 dB State	7.04	-	9,0	6.77	-	9.23	
	15.5 dB State	14.54	-	16.47	14.27	-	16.73	
Input Return Loss		-	15	-	-	15	-	dB
Output Return Loss		-	15	-	-	15	-	dB
Input P0.1 dB		-	24	-	-	24	-	dBm
Input IP3		-	42	-	-	42	-	dBm

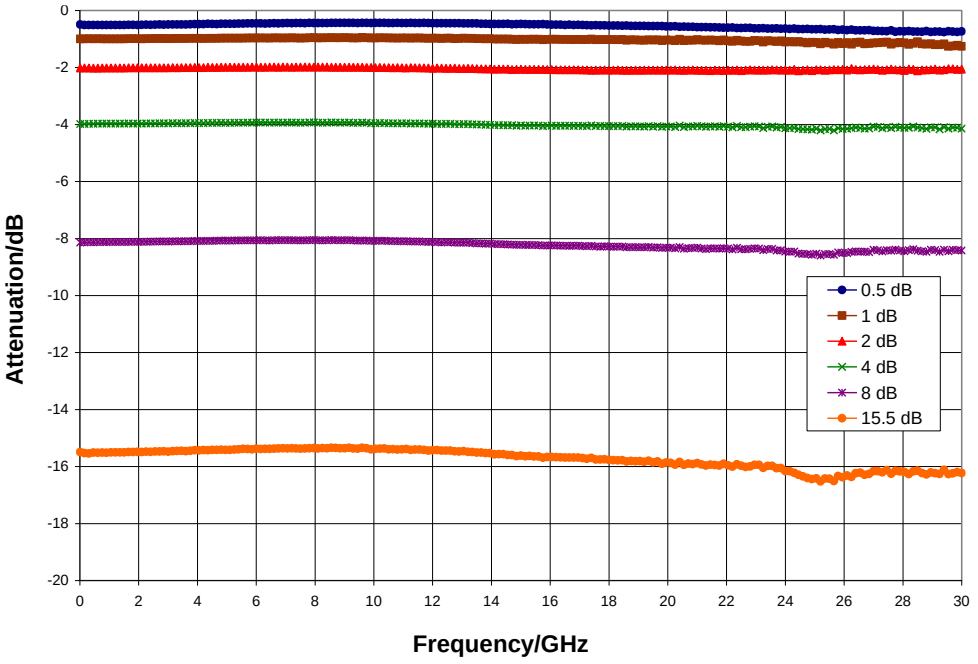
Note: Specification applies to major states

Typical Performance

Insertion Loss versus Temperature

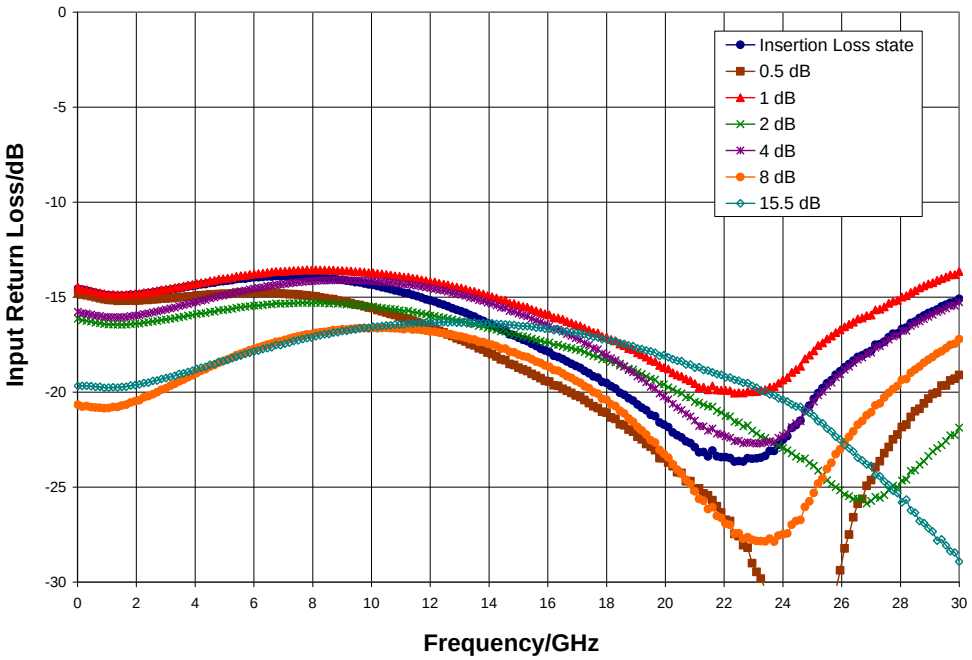


Normalized Attenuation (major states only), T_A = 25° C

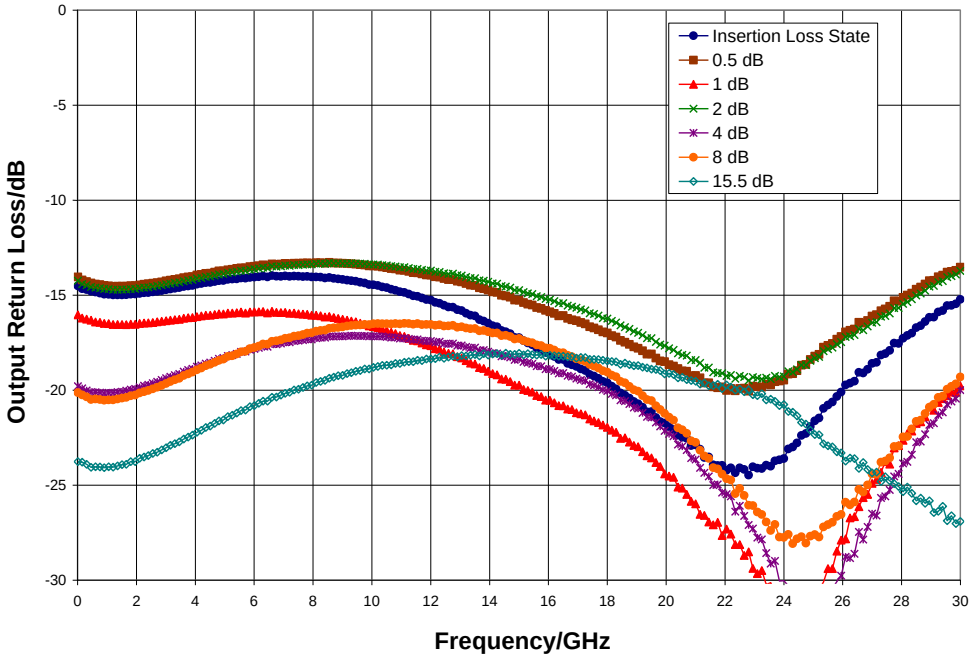


Typical Performance

Input Return Loss (major states only), T_A = 25° C

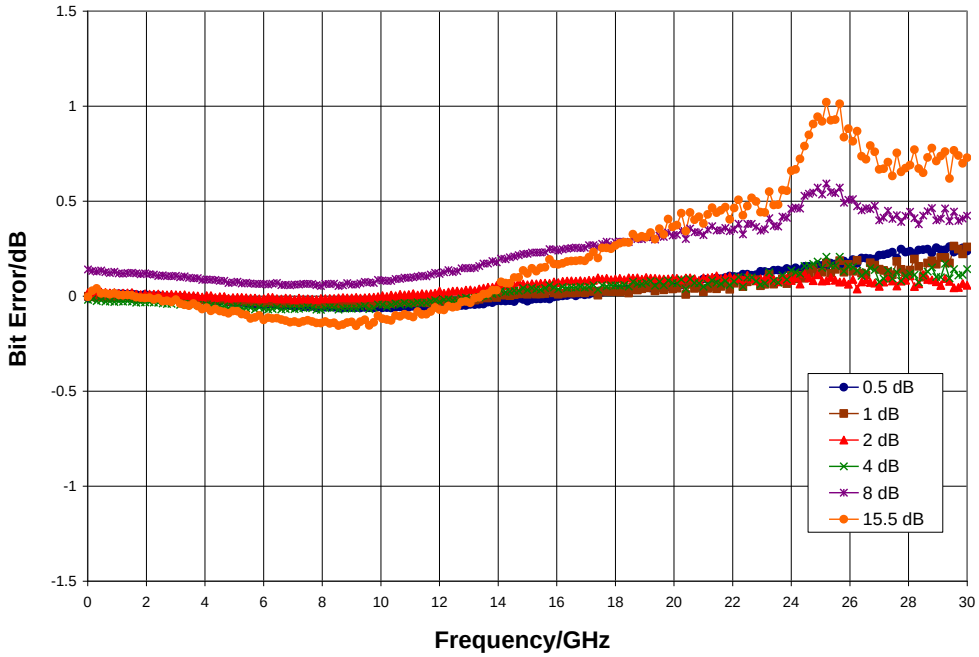


Output Return Loss (major states only), T_A = 25° C

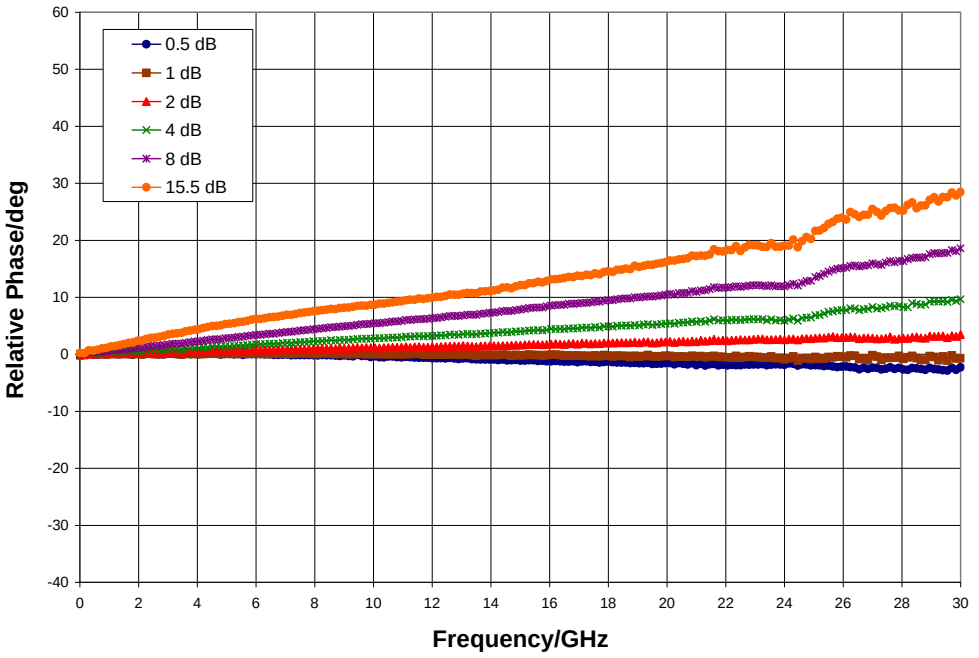


Typical Performance

Bit Error versus Frequency, T_A = 25° C

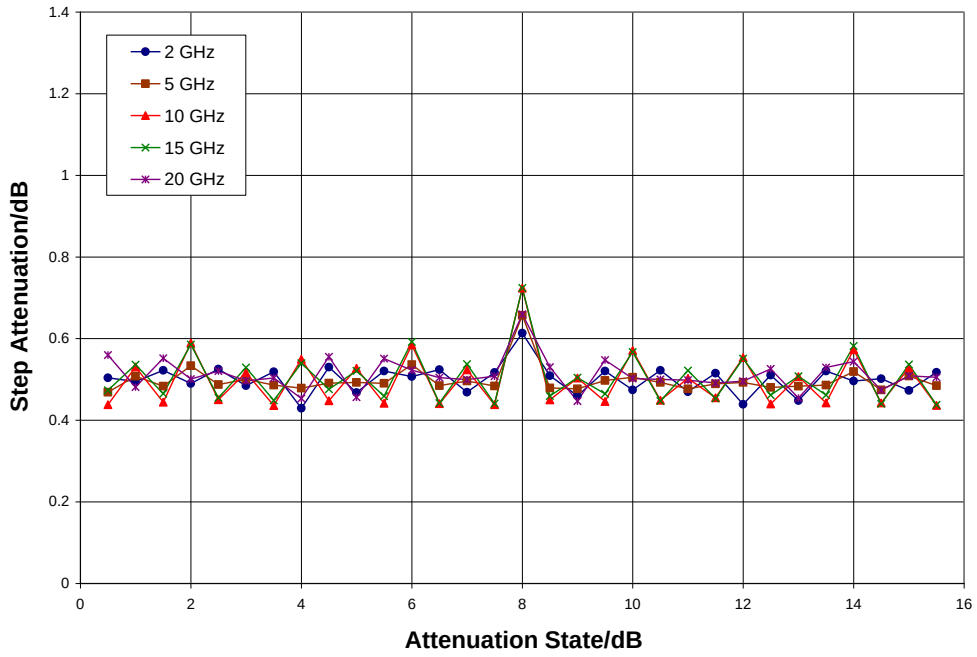


Relative Phase versus Frequency, T_A = 25° C

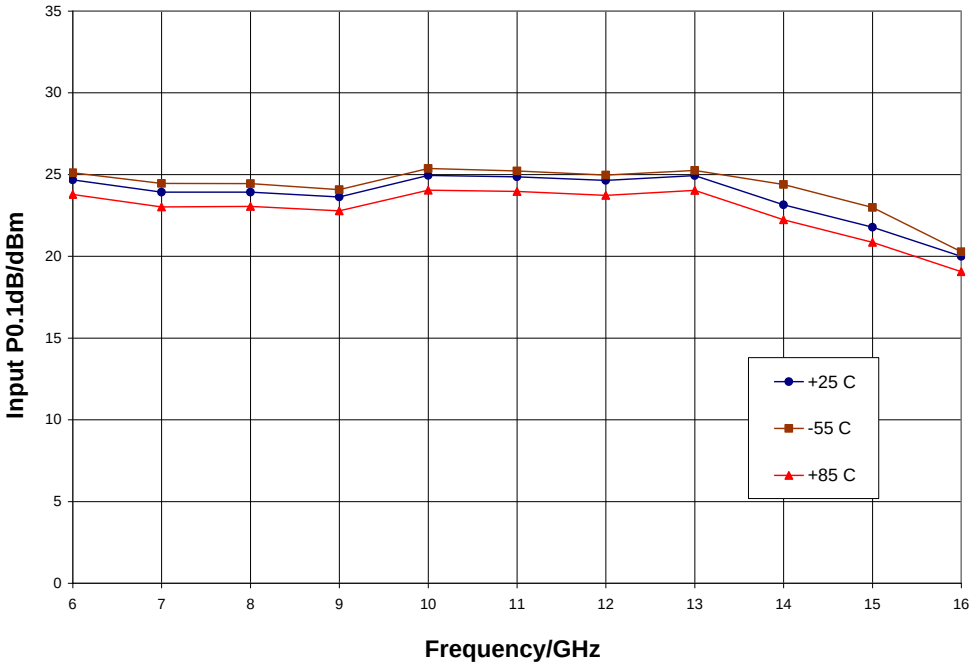


Typical Performance

Step Attenuation versus Attenuation State, T_A = 25° C

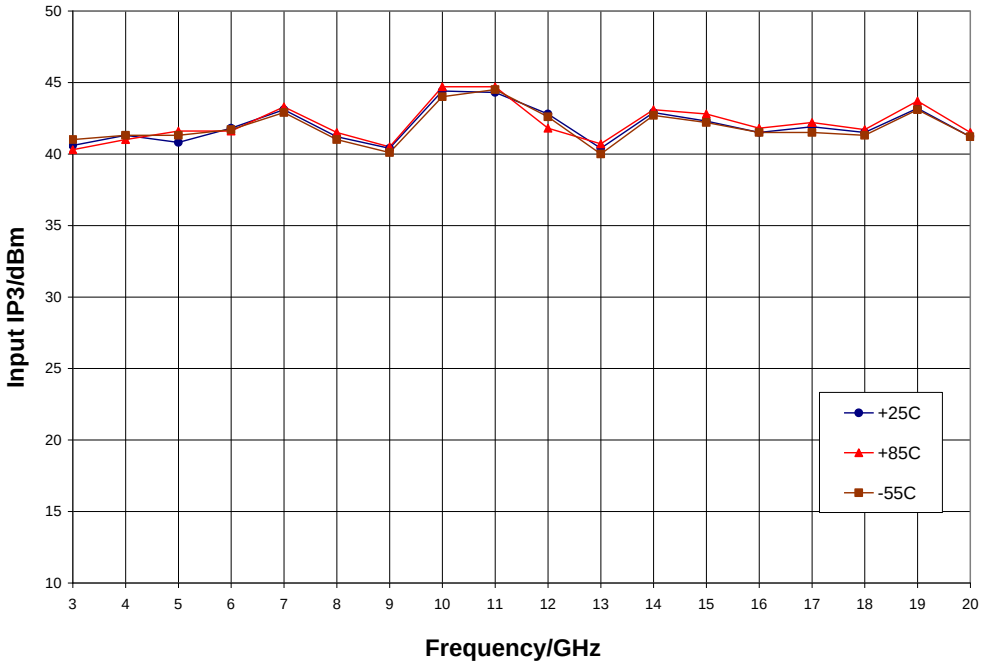


Input Power for 0.1 dB Compression (insertion loss state)



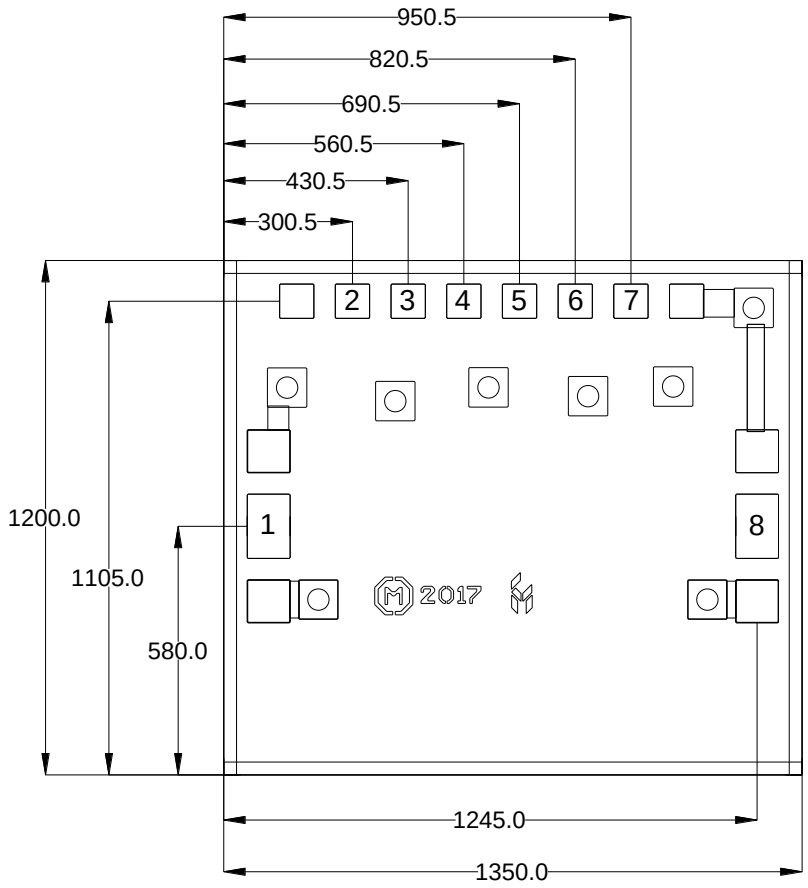
Typical Performance

Input IP3 versus Temperature (insertion loss state)



Mechanical Information

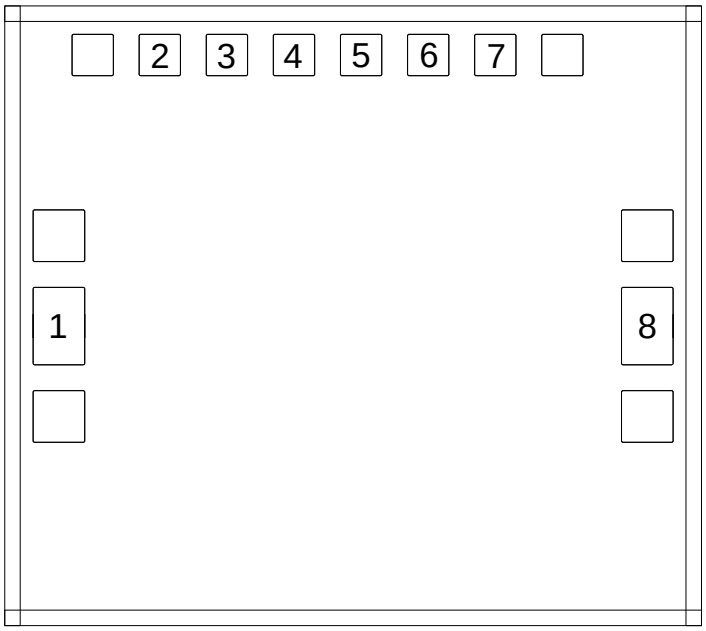
Die Outline (all dimensions in microns)



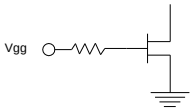
Notes:
1. No connection required for unlabeled pads
2. Backside is RF and DC ground
3. Backside and bond pad metal: Gold
4. Die is 100 microns thick
5. DC bond pads (2, 3, 4, 5, 6, 7) are 80 x 80 microns square
6. RF bond pads (1, 8) are 100 x 150 microns

Pad Description

Pad Diagram



Functional Description

Pad	Function	Description	Schematic
1, 8	RF1, RF2	50 ohm matched	
2	V_{ee}	Negative bias -5 V	
3, 4, 5, 6, 7	P0 - P4	Bit control voltages, see truth table for values	
Backside	Ground	Connect to RF / DC ground	

Applications Information

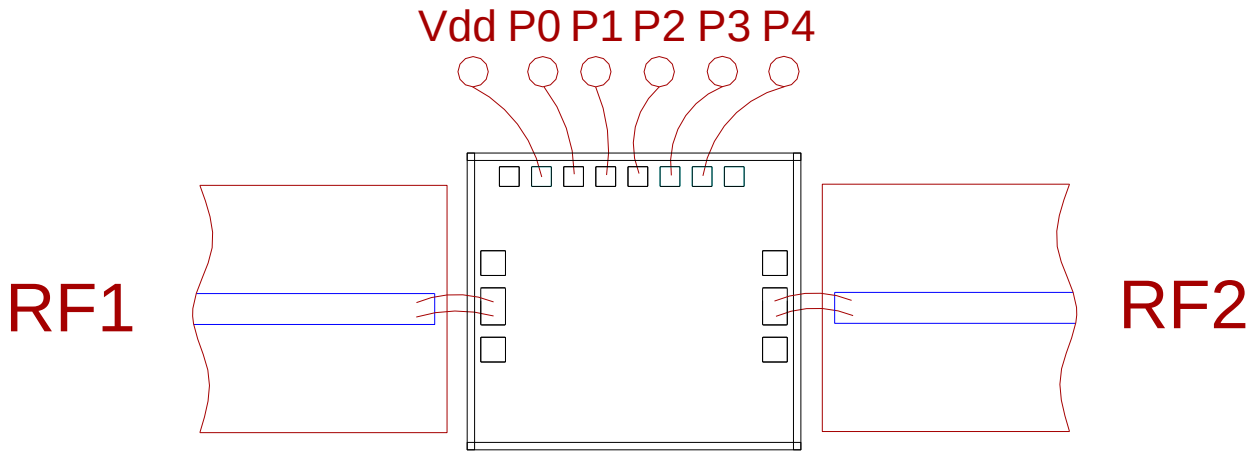
Assembly Guidelines

The backside of the CMD280 is RF ground. Die attach should be accomplished with electrically and thermally conductive epoxy only. Eutectic attach is not recommended. Standard assembly procedures should be followed for high frequency devices. The top surface of the semiconductor should be made planar to the adjacent RF transmission lines, and the RF decoupling capacitors placed in close proximity to the DC connections on chip.

RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized. The RF input and output require a single bond wire as shown.

The semiconductor is 100 um thick and should be handled by the sides of the die or with a custom collet. Do not make contact directly with the die surface as this will damage the monolithic circuitry. Handle with care.

Assembly Diagram



Biasing and Operation

The CMD280 has five control lines and a V_{ee} bias port. The CMD280 will not operate unless V_{ee} is applied to the MMIC.

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test

Handling Precautions

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	Class 1A	ESDA / JEDEC JS-001-2012

Caution!
ESD-Sensitive Device

RoHS Compliance

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Lead Free
- Antimony Free
- TBBP-A ($C_{15}H_{12}Br_4O_2$) Free
- SVHC Free
- Halogen Free
- PFOS Free

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

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